Power MOSFETS (cont'd)

ECG Type	Description and Application	Transconductance gfs µmhos	Drain to Source Breakdown Voltage BV_{DSS}	Gate to Source Breakdown Voltage BV_{GS}	Continuous Drain Current I_D Amps	Gate to Source Threshold Voltage V_{GS} (th)	Drain to Source Resistance r_{DS} (on) Ohms	Input Cap C_{iss} pf	Device Dissipation @T_C=25° C P_D Watts	Package Case/Fig./Basing
ECG2920 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	25 Min	60 Min	±20 Max*	70	4 Max	.014 Max	4000 Typ	200 Max	**TO-247** • Fig. T48-4
						td(off) = 400 ns, td(on) = 200 ns, tf = 300 ns, tr = 900 ns				
ECG2375 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	13 Min	100 Min	±20 Max*	40	4 Max	.055 Max	2000 Typ	180 Max	
						td(off) = 60 ns, td(on) = 15 ns, tf = 90 ns, tr =140 ns				
ECG2376 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	13 Min	200 Min	±20 Max*	30	4 Max	.085 Max	2000 Typ	180 Max	
						td(off) = 70 ns, td(on) = 20 ns, tf = 80 ns, tr = 125 ns				
ECG2921 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	250 Min	±20 Max*	15	4 Max	.28 Max	1400 Typ	150 Max	
						td(off) = 50 ns, td(on) = 20 ns, tf = 30 ns, tr = 60 ns				
ECG2922 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	400 Min	±20 Max*	16	4 Max	.3 Max	2900 Max	180 Max	• **TO-3PJ** Alt. Case Fig T48-1
						td(off) = 140 ns, td(on) = 40 ns, tf = 50 ns, tr = 115 ns				
ECG2923 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	500 Min	±20 max*	9	4 Max	.85 Max	1000 Typ	180 Max	
						td(off) = 50 ns, td(on) = 20 ns, tf = 30 ns, tr = 30 ns				
ECG2924 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	20 Min	600 Min	±20 max*	7	4 Max	1.3 Max	1000 Typ	180 Max	
						td(off) = 50 ns, td(on) = 20 ns, tf = 30 ns, tr = 25 ns				

Logic Level MOSFETS†

ECG Type	Description and Application	Transconductance gfs µmhos	Drain to Source Breakdown Voltage BV_{DSS}	Gate to Source Breakdown Voltage BV_{GS}	Continuous Drain Current I_D Amps	Gate to Source Threshold Voltage V_{GS} (th)	Drain to Source Resistance r_{DS} (on) Ohms	Input Cap C_{iss} pf	Device Dissipation @T_C=25° C P_D Watts	Package Case/Fig./Basing
ECG2984 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	60 Min	±15 Max*	15	2.5 Max	.15 Max	500 Max	70 Max	**TO-220** Fig. T41
						td(off) = 60 ns, td(on) = 90 ns, tf = 90 ns, tr = 190 ns				
ECG2985 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	10 Min	60 Min	±15 Max*	30	2..5 Max	.055 Max	1300 Max	100 Max	
						td(off) = 100 ns, td(on) = 90 ns, tf = 140 ns, tr = 460 ns				
ECG2986 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	17 Min	60 Min	±15 Max	50	2.5 Max	.028 Max	2600 Max	150 Max	
						td(off) = 150 ns, td(on) = 100 ns, tf = 220 ns, tr = 600 ns				
ECG2987 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	10 Min	100 Min	±15 Max*	20	2.5 Max	.12 Max	1500 Max	100 Max	
						td(off) = 80 ns, td(on) = 60 ns, tf = 80 ns, tr = 160 ns				
ECG2980 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	60 Min	±10 Max*	7	2 Max	.2 Max	400 Typ	25 Max	**TO-126N** Fig. T45-5
						td(off) = 20 ns, td(on) = 15 ns, tf = 30 ns, tr = 120 ns				
ECG2981 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	4 Min	100 Min	±10 Max*	7	2 Max	.27 Max	490 Typ	42 Max	
						td(off) = 25 ns, td(on) = 15 ns, tf = 30 ns, tr = 70 ns				

*Warning - Exceeding BVGS maximum will result in permanent damage to the gate region oxide layer.

▲ Refer to MOSFET Handling Precautions - Page 1 - 34

† Logic Level MOSFETS are fully enhanced when 5V is applied to the gate.

Package Outlines - See Page 1-91